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SiO2 Film (No Ar), Grown using Unaxis ICP PM3 Deposition Tool, Characterizations				
	50°C(ICP)	100°C(ICP)	250°C(ICP)	250°C(PECVD)
Refractive Index	1.465	1.467	1.472	N/A
Deposition Rate (nm/min.)	30.3	31.0	25.1	~40
Buffered HF Etch Rate (nm/min.)	187.5	211.2	168	520
Film Stress (~200 nm in Thickness) (MPa)	-334	-279	-271	-330

Figure 1. SiO2 deposited onto an etched GaAs structure at (a) 50°C; (b) 100°C.